

## Problem Set 1: MOS (Biasing + Small-Signal Model)

### Chapter 6 (MOS Device)

In the following problems, unless otherwise stated, assume  $\mu_n C_{ox} = 200 \mu\text{A}/\text{V}^2$ ,  $\mu_p C_{ox} = 100 \mu\text{A}/\text{V}^2$ , and  $V_{TH} = 0.4 \text{ V}$  for NMOS devices and  $-0.4 \text{ V}$  for PMOS

#### Problem 6.24

In the Fig. 6.42, what is the minimum allowable value of  $V_{DD}$  if  $M_1$  must not enter the triode region? Assume  $\lambda = 0$ .

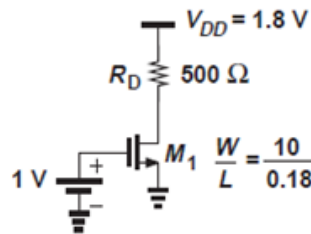


Figure 6.42

#### Problem 6.31

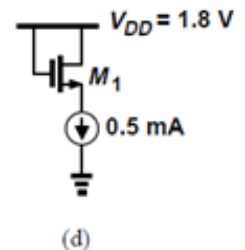
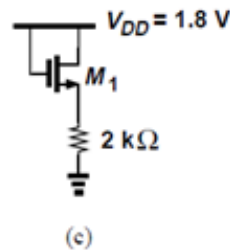
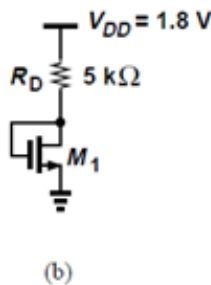
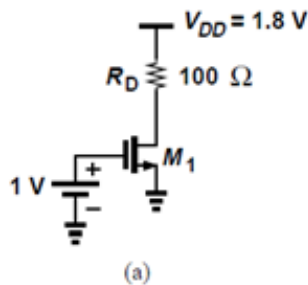
An NMOS device operating in saturation with  $\lambda = 0$  must provide a transconductance of  $1/(50 \Omega)$ .

- Determine  $W/L$  if  $I_D = 0.5 \text{ mA}$ .
- Determine  $W/L$  if  $V_{GS} - V_{TH} = 0.5 \text{ V}$ .
- Determine  $I_D$  if  $V_{GS} - V_{TH} = 0.5 \text{ V}$ .

#### Problem 6.33 (b, d)

If  $\lambda = 0.1 \text{ V}^{-1}$  and  $W/L = 20/0.18$ , construct the small-signal model of each of the circuits shown

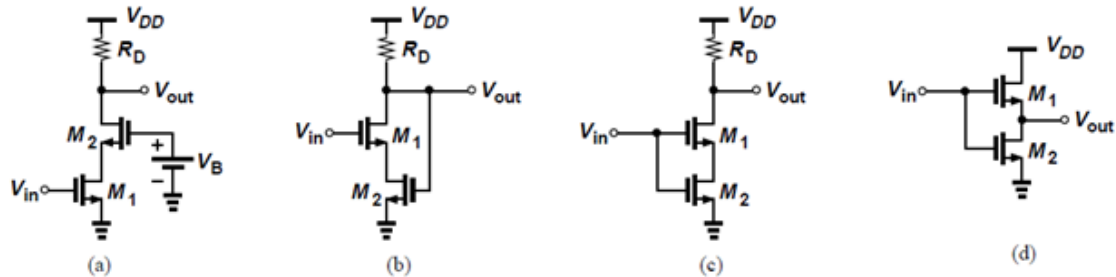
**Solve the DC operating point**



### Problem 6.38 (d)

Construct the small-signal model of the circuits depicted in Fig. 6.50. Assume all transistors operate in saturation and  $\lambda \neq 0$ .

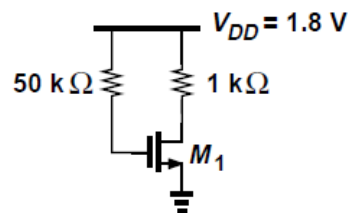
Find an expression for  $R_{in}$  and  $R_{out}$



## Chapter 7 (Biasing Techniques & Input / Output Impedance)

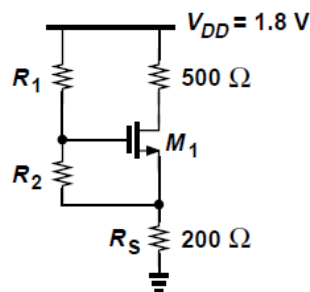
### Problem 7.1

In the circuit of Fig. 7.39, determine the maximum allowable value of  $W/L$  if  $M_1$  must remain in saturation. Assume  $\lambda = 0$ .



### Problem 7.5

Consider the circuit depicted in Fig. 7.43, where  $W/L = 20/0.18$ . Assuming the current flowing through  $R_2$  is one-tenth of  $I_{D1}$ , calculate the values of  $R_1$  and  $R_2$  so that  $I_{D1} = 0.5\text{ mA}$ .



### Problem 7.15

Consider the circuit shown in Fig. 7.52, where  $(W/L)_1 = 10/0.18$  and  $(W/L)_2 = 30/0.18$ , if  $\lambda = 0.1 \text{ V}^{-1}$ , calculate  $V_B$

